## DATA SHEET



## 1PS79SB10 <br> Schottky barrier diode

## FEATURES

- Low forward voltage
- Guard ring protected
- Ultra small plastic SMD package.


## APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes.


## DESCRIPTION

Planar Schottky barrier diode encapsulated in a SC-79 ultra small plastic SMD package.


## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :--- | :--- | :--- | :--- | :--- | :--- |
| $\mathrm{V}_{\mathrm{R}}$ | continuous reverse voltage |  | - | 30 | V |
| $\mathrm{I}_{\mathrm{F}}$ | continuous forward current |  | - | 200 | mA |
| $\mathrm{I}_{\text {FRM }}$ | repetitive peak forward current | $\mathrm{t}_{\mathrm{p}} \leq 1 \mathrm{~s} ; \delta \leq 0.5$ | - | 300 | mA |
| $\mathrm{I}_{\mathrm{FSM}}$ | non-repetitive peak forward current | $\mathrm{t}_{\mathrm{p}}<10 \mathrm{~ms}$ | - | 600 | mA |
| $\mathrm{~T}_{\text {stg }}$ | storage temperature |  | -65 | +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{j}}$ | junction temperature |  | - | 125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {amb }}$ | operating ambient temperature |  | -65 | +125 | ${ }^{\circ} \mathrm{C}$ |

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## ELECTRICAL CHARACTERISTICS

$\mathrm{T}_{\text {amb }}=25^{\circ} \mathrm{C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MAX. | UNIT |
| :--- | :--- | :--- | :--- | :--- |
| $\mathrm{V}_{\mathrm{F}}$ | continuous forward voltage | see Fig.2 |  |  |
|  |  | $\mathrm{I}_{\mathrm{F}}=0.1 \mathrm{~mA}$ | 240 | mV |
|  |  | $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA}$ | 320 | mV |
|  |  | $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$ | 500 | mV |
|  |  | $\mathrm{I}_{\mathrm{F}}=30 \mathrm{~mA}$ | mV |  |
|  |  | $\mathrm{I}_{\mathrm{F}}=100 \mathrm{~mA}$ | 800 | mV |
| $\mathrm{I}_{\mathrm{R}}$ | continuous reverse current | $\mathrm{V}_{\mathrm{R}}=25 \mathrm{~V} ;$ note 1; see Fig.3 | 2 | $\mu \mathrm{la}$ |
| $\mathrm{C}_{\mathrm{d}}$ | diode capacitance | $\mathrm{V}_{\mathrm{R}}=1 \mathrm{~V} ; \mathrm{f}=1 \mathrm{MHz}$; see Fig.4 | 10 | pF |

## Note

1. Pulsed test: $\mathrm{t}_{\mathrm{p}}=300 \mu \mathrm{~s} ; \delta=0.02$.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
| :--- | :--- | :--- | :---: | :---: |
| $R_{\text {th } j-a}$ | thermal resistance from junction to ambient | note 1 | 450 | K/W |

## Note

1. Refer to SC-79 standard mounting conditions.

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## GRAPHICAL DATA


(1) $\mathrm{T}_{\mathrm{amb}}=125^{\circ} \mathrm{C}$.
(2) $\mathrm{T}_{\text {amb }}=85^{\circ} \mathrm{C}$.
(3) $\mathrm{T}_{\text {amb }}=25^{\circ} \mathrm{C}$.

Fig. 2 Forward current as a function of forward voltage; typical values.
voltage; typical values.

(1) $\mathrm{T}_{\mathrm{amb}}=125^{\circ} \mathrm{C}$.
(2) $\mathrm{T}_{\text {amb }}=85^{\circ} \mathrm{C}$.
(3) $\mathrm{T}_{\text {amb }}=25^{\circ} \mathrm{C}$.

Fig. 3 Reverse current as a function of reverse
(3) $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$

$\mathrm{f}=1 \mathrm{MHz} ; \mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$.
Fig. 4 Diode capacitance as a function of reverse voltage; typical values.

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## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads


DIMENSIONS (mm are the original dimensions)

| UNIT | $\mathbf{A}$ | $\mathbf{b}_{\mathbf{p}}$ | $\mathbf{c}$ | $\mathbf{D}$ | $\mathbf{E}$ | $\mathbf{H}_{\mathbf{E}}$ | $\mathbf{v}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| mm | 0.65 | 0.34 | 0.17 | 1.25 | 0.85 | 1.65 | 0.1 |
|  | 0.58 | 0.26 | 0.11 | 1.15 | 0.75 | 1.55 |  |

Note

1. The marking bar indicates the cathode

| OUTLINE <br> VERSION | REFERENCES |  |  |  | EUROPEAN <br> PROJECTION | ISSUE DATE |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | IEC | JEDEC | JEITA |  |  |  |

## DATA SHEET STATUS

| DOCUMENT <br> STATUS |  |
| :--- | :--- | :--- |
| Objective data sheet | PRODUCT <br> STATUS |
| ${ }^{(2)}$ |  |$\quad$ Development | DEFINITION |
| :--- |
| This document contains data from the objective specification for product |
| development. |

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## Contact information

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